PATENT ASSIGNMENT COVER SHEET

Electronic Version v1.1 Stylesheet Version v1.2 EPAS ID: PAT2845946

SUBMISSION TYPE:	NEW ASSIGNMENT
NATURE OF CONVEYANCE:	ASSIGNMENT

CONVEYING PARTY DATA

Name	Execution Date
ANOBIT TECHNOLOGIES LTD.	06/01/2012

RECEIVING PARTY DATA

Name:	APPLE INC.
Street Address:	1 INFINITE LOOP
City:	CUPERTINO
State/Country:	CALIFORNIA
Postal Code:	95014

PROPERTY NUMBERS Total: 1

Property Type	Number
Application Number:	11995801

CORRESPONDENCE DATA

Fax Number: (512)853-8801

Correspondence will be sent to the e-mail address first; if that is unsuccessful, it will be sent via

US Mail.

Phone: 512-853-8800

Email: ezeiss@intprop.com

Correspondent Name: **ERIN ZEISS**

Address Line 1: 1120 S. CAPITAL OF TEXAS HGWY

Address Line 2: BLDG #2, SUITE 300 Address Line 4: AUSTIN, TEXAS 78746

ATTORNEY DOCKET NUMBER:	5888-73706
NAME OF SUBMITTER:	B. NOEL KIVLIN
SIGNATURE:	/B. Noel Kivlin/
DATE SIGNED:	05/07/2014

Total Attachments: 42

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EXHIBIT A –1 ASSIGNMENT OF PATENT RIGHTS

This patent assignment ("Patent Assignment") is entered into as of the below-date by and between Anobit Technologies Ltd., a company duly incorporated under the law of the State of Israel under Company Number 51-384451-4, with its registered office at 8 Hasadnaot St., Herzliya, Israel ("Assignor"), and Apple Inc., a California corporation with principal place of business at 1 Infinite Loop, Cupertino, CA 95014 ("Assignee").

For good and valuable consideration, the receipt and sufficiency of which is hereby acknowledged, Assignor does hereby irrevocably sell, assign, transfer, and convey unto Assignee or its designees all of Assignor's right, title, and interest, including without limitation, the right to sue or assert causes of action for past, present and future infringement, in and to all of the following (collectively, the "Patent Rights"):

- (a) the provisional patent applications, patent applications and patents listed in the attached Exhibit A-2 (the "Patents");
- (b) all provisional patent applications, patent applications, patents or other similar governmental grants or issuances (i) from which any of the Patents directly or indirectly claims priority and/or (ii) for which any of the Patents directly or indirectly forms a basis for priority;
- (c) reissues, re-examinations, extensions, continuations, continuations in part, continuing prosecution applications, requests for continuing examinations, and divisions of any item in the foregoing categories (a) and (b);
- (d) rights to all inventions claimed in any item in the foregoing categories (a) through (c);
- (e) items in any of the foregoing in categories (a) through (d), whether or not expressly listed as Patents below and whether or not claims in any of the foregoing have been rejected, withdrawn, cancelled, or the like;
- (f) rights to all inventions, invention disclosures, and discoveries described in any item in the foregoing categories (a) through (e), and all other rights arising out of such inventions, invention disclosures, and discoveries;
- (g) rights to apply in any or all countries of the world for patents, certificates of invention, utility models, industrial design protections, design patent protections, or other governmental grants or issuances of any type with respect to any inventions claimed in any item in the foregoing categories (a) through (c), including, without limitation, under the Paris Convention for the Protection of Industrial Property, the International Patent Cooperation Treaty, or any other convention, treaty, agreement, or understanding;
- (f) causes of action (whether currently pending, filed, or otherwise) and other enforcement rights under or on account of any of the Patents and/or any item in any of the foregoing categories (a) through (c), including, without limitation, all causes of action and other enforcement rights for (i) damages, (ii) injunctive relief, and (iii) other remedies of any kind for past, current, and future infringement; and
- (i) all rights to collect royalties and other payments under or on account of any of the Patents and/or any item in the foregoing categories (b) through (h).

Assignor hereby authorizes the respective patent office or governmental agency in each jurisdiction to issue any and all patents, certificates of invention, utility models or other governmental grants or

issuances that may be granted upon any of the Patent Rights in the name of Assignee, as the assignee to the entire interest therein.

The terms and conditions of this Assignment of Patent Rights will inure to the benefit of Assignee, its successors, assigns, and other legal representatives and will be binding upon Assignor, its successors, assigns, and other legal representatives.

This Assignment of Patent Rights is being entered into in connection with that certain Intellectual Property Purchase Agreement between Assignor and Assignee. If there is any inconsistency between this Assignment of Patent Rights and such Intellectual Property Purchase Agreement, the Intellectual Property Purchase Agreement shall prevail.

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Signed at Santa Clara County, California USA on L June 2012

ASSIGNOR

For and on behalf of ANOBIT TECHNOLOGIES LTD.

Name: Elizabeth S. Rafael

Title: Director Date: ∠ June 2012

ASSIGNEE

For and on behalf of: APPLE INC.

Name: Gene Levoff Title: Assistant Secretary Date: __ June 2012

EXHIBIT A –2 LIST OF PATENTS ASSIGNED UNDER ASSIGNMENT OF PATENT RIGHTS (EXHIBIT A-1)

EXHIBIT A-2
LIST OF PATENTS ASSIGNED UNDER EXHIBIT A-1 ASSIGNMENT OF PATENT RIGHTS

Country	Patent Number	Application Number	Publication Number	Title
US		61471148	N/A	Recovery from read failures in NAND flash by using volatile memory.
US	***************************************	60747106	N/A	DSP and coding algorithms
US		60806533	N/A	High Density Memory Systems and Methods
US		60821764	N/A	Algorithms for programming and reading memory devices Additional files: Coding and Decoding Algorithms for Memory Devices Method for Feedback Coded Programming in Memory Devices Non-Linear Equalization in Flash Memories
US		60822236	N/A	Algorithms for Increasing Density and Robustness of Memory Devices Additional File: Dynamic data-rate allocation, Precoding for combating impulsive noise
US		60823650	N/A	Algorithms for Measuring and Estimating Coupling Ratios in Memory Devices
US		60825913	N/A	New Methods for Non-Volatile Memory
US		60825917	N/A	Methods for Reducing Coupling Effect in Memory Devices

US	60827067	N/A	Methods for Mitigating Disturb Noise in Memory Devices
US	60862611	N/A	A Method for High Speed Access to Multi-Level Memory Devices Using Variable Accuracy Programming
US	60862612	N/A	Dynamic programming rate allocation for memory devices
US	60863480	N/A	A Method to Combat Aging and Crosstalk in Flash Memory Devices
US	60863491	N/A	Improved Programming Speed & reliability, by improvement the P&V
US	60863506	N/A	Reading & Programming Methods in memory devices
US	60863810	N/A	Methods for High Resolution Sampling and Feedback Codes in Memory Devices Feedback Codes (Re-submitted - 16 on 1/11/2006)
US	60865653	N/A	High-speed interface
US	60865665	N/A	Training sequences
US	60866071	N/A	Improved Programming Cycle of Memory Devices
US	60866860	N/A	Capacity Management in memory devices
US	60867204	N/A	Architecture of high density, high performance memory devices
US	60867399	N/A	Architecture of high density, high performance memory devices

US	60867401	N/A	Efficient Methods for Mitigating Disturb Noise in Memory Devices
US	60868342	N/A	Methods to optimize memory devices structure using a Digital Signal Processor
US	60868549	N/A	Methods to compensate on Sense Amplifier mismatch
US	60868731	N/A	Method to improve memory devices testing
US	60870398	N/A	Application Dependent Memory Device Interface
US	60870399	N/A	Methods to improve memory devices latency
US	60871838	N/A	Usage of Bad Blocks to Increase Capacity
US	60882240	N/A	Memory device in which the size of the input and output pages is different than the actual capacity of a page
US	60883061	N/A	An Extension to Memory Device
US	60883071	N/A	Method for assessing memory capacity and optimizing memory utilization based on measuring the time periods between programming operations
US	60885024	N/A	Method for Mitigating Errors in Memory Devices that Combines DSP and Analog Program and Verify Algorithms
US	60885987	N/A	Combined Capacity Management and Coding Schemes for memory devices

US	60886102	N/A	Combined Interference Mitigation and Disturb Mitigation with Coding Schemes for Memory Devices
US	60886429	N/A	Methods for Error Estimations in Memory Array
US	60886450	N/A	Methods for Error Estimations in Memory Array
US	60888599	N/A	Adaptive Step Pulse Programming Scheme for Memory Devices
US	60888828	N/A	Parameter Optimization in memory devices
US	60889277	N/A	Parameter Optimization in memory devices
US	60889279	N/A	A detection device with a serial output
US	60891568	N/A	Back Pattern Dependency Estimation
US	60891569	N/A	Back Pattern Dependency Estimation
US	60892869	N/A	Methods to Implement a Combined Interference Mitigation and Disturb Mitigation with Coding Schemes for Memory Devices
US	60893142	N/A	Multi Level Read Algorithm
US	60894290	N/A	Methods to Calculate the Optimized Thresholds for Reading Memory Devices
US	60894456	N/A	Methods to Cancel Crosstalk in Memory Devices
US	60895746	N/A	Reduce Power Peaks in Multi-Components Systems

US	60895748	N/A	Methods to Optimize ECC and EDC power and typical latency in memory
US	60896275	N/A	Methods to Reduce Die Size Area of Memory Devices
US	60912056	N/A	Command Set Extension for Memory Devices
US	60913281	N/A	Command Set Extension for Memory Devices
US	60915540	N/A	Reducing margins in voltage levels of memory devices
US	60915689	N/A	Reducing margins in voltage levels of memory devices
US	60916877	N/A	Bit Mappings for Multi Level Cells Memory Devices
US	60916888	N/A	Reducing margins for the erased level in MLC memory devices
US	60917649	N/A	Fragment Coding for Memory devices
US	60917651	N/A	Performance Optimization method for systems accessed as slaves
US	60917652	N/A	Efficient method for distinguishing between full and partial programmed memory
US US	60917653	N/A	Methods to Improve Memory Device Functionality
US	60938192	N/A	Combating Back Pattern Dependency and Other Distortions in Flash Memory Devices Using Re-read with Modified Read Parameters

US	60939076	N/A	Cell Group Parameters Adjustments According Noise Margin
US	60939077	N/A	Estimation and Calibration Methods for Memory Devices
US	60940404	N/A	Bit Mappings for Multi Level Cells Memory Devices
US	60941673	N/A	Memory Devices Using Non-Rectangular Cell Array
US	60943613	N/A	Allocating and ordering of pages in MLC memory devices
US	60943745	N/A	Detecting Number of Programmed Pages
US	60943843	N/A	Power Reduction of Electronic Devices with Memory
US	60946218	N/A	Protected Cells in MLC Memory Devices
US	60947427	N/A	Improving the program and verify process of memory devices
US	60947428	N/A	Improving programming speed of memory devices
US	60947970	N/A	Interference mitigation using individual word line erasure operations
US	60948783	N/A	Improving P&V Scheme
US	60948844	N/A	Methods to calculate the optimal ISPP
US	60948995	N/A	Allocation of multi level translation table
US	60949515	N/A	Improved coding schemes for memory devices with non-uniform error rate

US	60949891	N/A	Methods to Improve DRAM performance
US	60950884	N/A	Methods to calculate Soft Metrics from memory device cells
US	60951215	N/A	Methods to calculate Soft Metrics from memory device cells
US	60952276	N/A	Method for Programming Memory Devices that are Robust to Programming Disturbs
US	60952572	N/A	Improved P&V Scheme to Reduce Cross-Talk Variance
US	60954010	N/A	Improve Utilization of Redundancy & Spare Bits within Memory Devices
US	60954012	N/A	Improve Utilization of Redundancy & Spare Bits within Memory Devices
US	60954013	N/A	Memory Controller with Variable Redundancy Requirements
US	60954163	N/A	Improve Read Throughput of Memory Device
US	60954169	N/A	Methods for Preventing Program Errors in Memory Devices
US	60954317	N/A	Method for Improving Programming Speed of Multi-Level Cell Memory Devices without Compromising Reliability
US	60956931	N/A	Novel Algorithms for Distortion Estimations in Memory Devices

US	60968317	N/A	Method to decrease number of Errors in Flash memory devices in case of Binary Bit Mapping
US	60968656	N/A	Methods to Ensure Specific Blocks in Memory Devices are Valid
US	60970058	N/A	Method for Improving Programming Speed of Multi-Level Cell Memory Devices without Compromising Reliability
US	60971593	N/A	A method to improve mitigation of failed memory programming
US	60971600	N/A	An Interface between Memory Extension and Memory Controller
US	60973452	N/A	Method for Combating Programming and Reading Memory Devices using Measurements of the Duration of Programming and Erase Operations
US	60973453	N/A	Method for Programming Memory Devices
US	60976435	N/A	Winding Geometry for Memory Device
US	60976436	N/A	Additional Methods to Incorporate Signal Processing Module on Memory Devices
US	60978146	N/A	A Method for Reliable Programming of Flash Devices in the Presence of Temperature Variations
US	60978767	N/A	A method for generating random numbers using flash memory

US	60978769	N/A	A method for counting number of events and maintaining the counter in a memory
US	60981113	N/A	A method for reading soft values from a memory device
US	60981114	N/A	Estimate and Mitigate Disturbs and Coupling in Erased Level in Memory Devices
US	60981116	N/A	Methods for Combating Voltage Shift In Memory Devices
US	60981117	N/A	Methods for Combating Erase Failure In Memory Devices
US	60982480	N/A	Methods for Combating Voltage Shift In Memory Devices
US	60983270	N/A	Securing configuration commands to memory devices
US	60983272	N/A	Methods for Combating Voltage Shift In Memory Devices
US	60983604	N/A	Reverse Programming Method for Non-Volatile Memories
US	60983950	N/A	Combined Coding and Program and Verify method
US	60985236	N/A	Programming algorithm in MLC memory devices
US	60987106	N/A	Adaptive Allocation of Reference Cells in Memory Devices
US	60987417	N/A	Optimized Packing of Variable Capacity Memory Chips in a multi-chip Product

US	60987632	N/A	Methods to Reduce Power Peaks of a Memory Storage System
US	60989129	N/A	Optimization of sampling in flash memories
US	60989812	N/A	Method and Apparatus for Incremental Coding in Memory Devices
US	60991245	N/A	Method to reduce number of read operations during erroneous event in Flash devices
US	60991246	N/A	A method to adjust reading thresholds
US	61012424	N/A	A Programming Scheme for Memory Devices
US	61012933	N/A	A Programming Scheme for Memory Devices
US	61013027	N/A	Method to efficiently perform random access read in Flash devices
US	61013032	N/A	Method to efficiently cancel interference in Flash devices
US	61014048	N/A	Programming Method for Multi-Plane Memory Device
US	61016566	N/A	Method to efficiently perform random access read in Flash devices
US	61016568	N/A	Cyclic Array of Blocks for File System Tables In Memory Devices
US	61016569	N/A	Using Mirrored Blocks in Memory Devices
US	61016570	N/A	Methods to Improve Read Throughput in the Event of Distortion Cancellation

US	61016816	N/A	A Memory Device with Indications to a Memory Controller
US	61016824	N/A	Additional Methods to Calculate the Optimized Thresholds for Reading Memory Devices
US	61017177	N/A	Additional Methods to Calculate the Optimized Thresholds for Reading Memory Devices
US	61022340	N/A	Improving Program Throughput of a Memory Device
US	61022343	N/A	MEMORY CELLS WITH NON-UNIFORM PROGRAMMING LEVELS
US	61022364	N/A	Enhancement of Error correction code using random bit inversion
US	61024561	N/A	Methods to Read Soft Values from Memory Device with minimal Throughput Penalty
US	61026150	N/A	Using the parity check equations of an error correction code to estimate and track parameters
US	61026211	N/A	Fast Cycling Level Estimation
US	61028226	N/A	A Memory Device with Integrated Memory Buffer and Logic
US	61029428	N/A	Indication of Cell Status within a Memory Device
US	61030240	N/A	Open loop NVRAM programming for increasing write throughput

US	61030972	N/A	Method to reduce variance of FLASH cells after retention
US	61031711	N/A	Method of Joint decoding in FLASH memories
US	61031712	N/A	Open loop NVRAM programming for increasing write throughput
US	61034511	N/A	Reading Combined Soft and Hard Information from Memory Devices
US	61037327	N/A	Reduced Sense time for Flash Devices
US	61037328	N/A	Enhancement of Error correction code using systematic bit inversions
US	61038758	N/A	Temperature and Wear Level Estimation and Calibration
US	61039109	N/A	Re-using Bad Blocks in Memory Devices
US	61039813	N/A	Improving Iterative Decoding Using Added LLR Information
US	61040800	N/A	Combined Replaced Cells Information into Distortion Estimation Procedure
US	61041600	N/A	Combined Replaced Cells Information into Distortion Estimation Procedure
US	61043733	N/A	Testing Procedure for a Memory System with Correction Capabilities
US	61043734	N/A	Reducing the peak Power consumption of ECC decoders
US	61043736	N/A	Reducing the average Power consumption of ECC decoders

US	61045627	N/A	Avoiding BPD errors due to temperature shift
US	61045628	N/A	Methods for Combating Voltage Shift In Memory Devices
US	61046807	N/A	A system with HDD and SSD
US	61046809	N/A	A method to improve HDD Operation
US	61048191	N/A	Wear level estimation for Flash devices
US	61048558	N/A	Efficient Implementation of Program-After-Erase in Memory Devices
US	61048669	N/A	A method for adaptively adjusting PV levels of the memory devices
US	61052276	N/A	Method of Hybrid decoding in FLASH memories
US	61053027	N/A	Wear level estimation for Flash devices
US	61053029	N/A	Efficient Implementation of Program-After-Erase in Memory Devices
US	61053030	N/A	A method for adaptively adjusting PV levels of the memory devices
US	61053031	N/A	Method of Hybrid decoding in FLASH memories
US	61054493	N/A	A New Programming Scheme for Memory Devices
US	61056488	N/A	Adaptive Program parameters for Flash devices
US	61057827	N/A	Method to calculate interference for memory device cells

US	61060486	N/A	Synchronization among storage devices in a RAID SSD system
US	61061685	N/A	Optimized Syndrome calculation for BCH decoders
US	61061689	N/A	Memory Devices Using Non-Rectangular Cell Array
US	61074643	N/A	Memory block sorting based on usage
US	61074644	N/A	Battery operated flash module
US	61076160	N/A	A New Programming Scheme for Memory Devices
US	61076161	N/A	Memory block sorting based on usage
US	61076163	N/A	Battery operated flash module
US	61076192	N/A	Programming the USB to MSB levels
US	61076647	N/A	Fast Recovery from Erase Failures
US	61076745	N/A	Modified Erase Verify Procedure
US	61076748	N/A	Using Bad Blocks List to Enlarge the Redundant Block List
US	61077182	N/A	Use of SLC area to improve read performance while performing XT cancellation
US	61077183	N/A	Marking Erased Sectors in the Binary Cache
US	61078405	N/A	Improved Read Performance of MLC Blocks using Binary Cache Method and XTALK Cancellation

US	61078777	N/A	Multi-Plane Internal Copy Back using Uncoupled Pages
US	61078778	N/A	Improved Read Performance of MLC Blocks using Binary Cache Method and XTALK Cancellation
US	61078780	N/A	A method for a memory controller to read at thresholds outside memory device boundaries
US	61078782	N/A	A method for a MLC memory device controller to restore data from mixed levels
US	61079140	N/A	Insertion of Gaps in Binary Cache for non Programmed Pages
US	61079141	N/A	Using Snapshots in the Binary Cache for Faster Recovery Time
US	61080877	N/A	Modified Erase Verify Procedure
US	61081047	N/A	Using Snapshots in the Binary Cache for Faster Recovery Time
US	61082231	N/A	Binary Cache Configuration for Enhancing Programming Performance
US	61082233	N/A	Multi-Plane Internal Copy Back using Uncoupled Pages
US	61086164	N/A	A method for efficient data recovery of multi-bit per cell memory devices during power failure
US	61086225	N/A	Program & Read parameters change for Memory devices

US	61086541	N/A	A method for efficient data recovery of multi-bit per cell memory devices during power failure
US	61093334	N/A	Joint Programming Schemes for Memory Devices
US	61093366	N/A	Modified Erase Verify Procedure
US	61093367	N/A	Multi-Plane Internal Copy Back using Uncoupled Pages
US	61093368	N/A	Using Bad Blocks List to Enlarge the Redundant Block List
US	61093369	N/A	Modified Erase Verify Procedure
US	61093461	N/A	A method for efficient data recovery of multi-bit per cell memory devices during power failure
US	61093578	N/A	Using bad blocks in SSD
US	61093596	N/A	Battery operated flash module
US	61093610	N/A	SSD Curing
US	61093613	N/A	ECC segmentation
US	61093621	N/A	Sequential and random partition
US	61093632	N/A	Local flash curing
US	61093722	N/A	Method for forecasting flash condition
US	61093723	N/A	Best available block metric
US	61093724	N/A	SSD Flash module
US	61093727	N/A	Diagnosis through Life Time and Self Healing Memory Device

US	61094066	N/A	Chip level fail recovery on SSD
US	61094417	N/A	Global Wear Leveling for Memory Devices
US	61096805	N/A	Methods to calculate the optimal ISPP
US	61096806	N/A	Peak Sample & Jump method
US	61096807	N/A	Method for Saving SSD and Memory Devices Power
US	61096808	N/A	Power Efficient Method for Refreshing Memory
US	61097224	N/A	Faster Programming method
US	61098829	N/A	Improved Copy Back Procedure
US	61105454	N/A	Chien Search Using Serial Multipliers
US	61105580	N/A	Using Low-Speed Random Access Device To Protect Data Stored in High-Speed Random Access Device
US	61105580	N/A	Methods for Error Correction in Storage Systems
US	61105630	N/A	Endurance improvement of flash memories in a file system environment
US	61105814	N/A	Usage of Binary Cache in a Multi-Die Memory System
US	61105816	N/A	A Method to Handle Program Failure Cases
US	61105818	N/A	Improving Capacity, endurance and reliability of solid-state disks

US	61105819	N/A	Method for combating retention errors during un-plugged storage of memory devices
US	61109767	N/A	Methods to Generate Scrambler Seed in memory devices
US	61112195	N/A	Efficient raid implementation
U5	61114473	N/A	Optimized Encoder supporting multiple cyclic codes
US	61115085	N/A	A method for equal-division of cells among levels for improving read performance
US	61115086	N/A	Storing M bits/cell using an N bits/cell device, where N <m< td=""></m<>
US	61118630	N/A	Modified Erase Verify Procedure
US US	61118632	N/A	A Method to Handle Program Failure Cases
US	61119929	N/A	Co-existence and cooperation between on-memory and external signal processing algorithms to combat memory cell impairments
US	61119950	N/A	Page Reordering method to improve read performance while performing XT cancellation or acquisition
US	61120968	N/A	Flash Reliable Mode
US	61120980	N/A	Refresh mechanism for non-volatile memories using Re-programming of the same page
US	61120987	N/A	Method to reduce number of Erasures in NAND device

US	61141830	N/A	A Memory Device Interface with Additional Commands
US	61141842	N/A	A method for overhauling SSD and non-volatile memory devices
US	61141855	N/A	Wider Programming for upper level for Flash devices
US	61141866	N/A	Dynamic Over-Provisioning Algorithm that can Improve the Reliability of Memory Devices
US	61144629	N/A	Methods for storing M bits/cell using an N bits/cell device, where N <m< td=""></m<>
US	61145562	N/A	Hierarchal Storage Device Management System
US	61145974	N/A	Randomizing data in hard drive
US	61151189	N/A	Flash solid state disk dynamic power management
US	61152073	N/A	Cooperative power management in a multiple flash SSD device
US	61156520	N/A	Memory Device with Adjustable & Adaptive Verify Scheme
US	61157599	N/A	Enhanced Control over Flash Partial Blocks
US	61158374	N/A	Method of Joint decoding in FLASH memories
US	61162310	N/A	Method to Improve Program Reliability for Multi Level NAND devices
US	61163129	N/A	Reduction of Program Errors using XT Procedure

US	61163133	N/A	Memory Controller with External DRAM Capabilities
US	61163138	N/A	Flash Read Threshold DataBase operation
US	61163146	N/A	Bit Reversal metric for iterative decoders
US	61168604	N/A	Improved re-Program operation
US	61168605	N/A	Methods for Efficient Copy from Binary Cache to MLC Area in Memory Devices
US	61171089	N/A	SSD rapid format
US	61171092	N/A	Drive locking
US	61172833	N/A	Improved Soft Sample Operation in Non-Volatile Memory
US	61175030	N/A	A Method for Optimal Thresholds Estimation
US	61176949	N/A	Utilizing SLC Cache scheme in a Memory Device
US	61180156	N/A	Reduce System Overhead during Read Operation from Memory Device
US	61181678	N/A	Higher Program Voltage for special SLC Word Lines
US	61182763	N/A	Varying verify bias during PV process
US	61187676	N/A	Improving Memory Device Operation by Varying Vpass
US	61218080	N/A	Improving Memory Device Operation by Varying Vpass
US	61221582	N/A	Chien Search Using Multiple basis representation

US	61224897	N/A	Dynamic allocation of SLC/MLC according to estimated heat distribution
US	61225929	N/A	Programming the USB to MSB levels
US	61229780	N/A	Allocating blocks for testing and monitoring
US	61229788	N/A	Design of Rate Compatible codes
US	61229793	N/A	Efficient Interference coefficient measurement
US	61230127	N/A	Handling Program Failure Cases
US	61234688	N/A	Systems and method for curing element in memory element array
US	61234695	N/A	Using a memory device with Fast and Enhanced read modes
US	61234699	N/A	Efficient Decoding of Error Correction Codes (ECC)
US	61240280	N/A	NAND block Unified conditioning
US	61243726	N/A	Memory Device Curing
US	61244493	N/A	SSD Flash module
US	61244500	N/A	Diagnosis through Life Time and Self Healing Memory Device
US	61244506	N/A	Joint Programming Schemes for Memory Devices
US	61246999	N/A	Improve Program Throughput by reordering pages
US	61248915	N/A	Chien Search Latency reduction

US	61251787	N/A	Methods for estimating block's condition during operation time
US	61251807	N/A	Encoding the modulo 2 sum of different pages in a flash device in order to decrease the probability of page failures
US	61251829	N/A	Hard LDPC Bit Flipping Decoding Using 2 Bits For Every Information Node
US	61251836	N/A	Efficient End To End Data Protection Method in Flash Storage Systems
US	61256200	N/A	Reduce Read thresholds sets
US	61262568	N/A	A Method for Measuring Read Disturb
US	61263836	N/A	Method of maintaining quality of service for Random Access Memories Perfect Bank DRAM
US	61263859	N/A	Interleaved ECC method for Random Access Memories
US	61264673	N/A	Efficient readout schemes for analog memory cell devices
US	61264809	N/A	LLR Unit Architecture
US	61265763	N/A	Wordline Issue
US	61286814	N/A	SSD – Read and Write performance balancing
US	61290547	N/A	Method of data compression for flash based storage devices
US	61290552	N/A	Offline methods of data compression for flash based storage devices

US	61290559	N/A	Accelerated data programming method for flash devices
US	61292229	N/A	Recipe Command & Status
US	61293676	N/A	Hibernation Storage Area Usage for Over Provisioning during Activity Time
US	61293808	N/A	Recovery from memory device failure using redundancy
US	61293814	N/A	Method for error correction using remote data storage
US	61294498	N/A	Varying verify bias during PV process
US	61301302	N/A	Termination criteria for iterative decoders
US	61303415	N/A	LDPC code design for optimized performance
US	61324429	N/A	Reuse of host hibernation storage space by memory controller
US	61326269	N/A	Special read commands for Efficient interference cancellation and soft ECC decoding for memory devices
US	61326858	N/A	special areas - v1
US	61330961	N/A	Improved Soft Sample Operation in Non-Volatile Memory
US	61330970	N/A	Special read commands for Efficient interference cancellation and soft ECC decoding for memory devices

US	61330989	N/A	Efficient copy and program commands with an option to stop/ resume or to break long operations to short steps
US	61334606	N/A	Adaptive over- provisioning in memory systems
US	61356521	N/A	sending address after data while programming NAND FLASH.
US	61357114	N/A	Current Peaks Smoothing
US	61358970	N/A	Constant Bit Rate Streaming Command for Storage Systems
US	61361458	N/A	Determining read threshold sets and optimizing their usage
US	61361946	N/A	Pipeline Management SSD
US	61363248	N/A	Shaping Methods for Combating Voltage Range Degradation Due to Shift Effects In Memory Arrays
US	61363655	N/A	Handling power failures and program failures in memory devices
US	61364198	N/A	NAND Soft Read Cache
US	61364406	N/A	Redundant data storage in multi die memory system
US	61367894	N/A	Read and Write Cache in hybrid drives
US	61369667	N/A	Program non integer bits per cell across wordlines
US	61369719	N/A	Avoid selecting last punched block

US	61369764	N/A	Codes for multi-die
			redundancy
US	61370817	N/A	High Endurance Cache in Flash
			Memory Devices
US	61372913	N/A	Combating the cell to cell
			interference to erased cells
US	61372921	N/A	Combating the cell to cell
			interference to erased cells
US	61373883	N/A	Redundant data storage in
			multi die memory system
US	61374377	N/A	Soft ECC Direction
US	61380233	N/A	A method for fast
			programming of NAND memory devices in a manner
			that reduces voltage shifts of
			erased cells
US	61386570	N/A	Optimization of Hybrid Disk
			performance
US	61386633	N/A	NAND block Unified
			conditioning
US	61390193	N/A	Special read commands for
			Efficient interference cancellation and soft ECC
			decoding for
			memory devices
US	61406610	N/A	NAND Soft Read Cache
US	61408659	N/A	Battery-less SSD that is Robust
			to Power Failures and Holds
			Variables in RAM
US	61417218	N/A	Differential Level
***************************************			Programming
US	61417315	N/A	Shaping Methods for
			Combating Voltage Range
			Degradation Due to Shift Effects
			In Memory Arrays

US	61417429	N/A	NV memory system optimizations
US	61417433	N/A	NV memory system optimizations
US	61419922	N/A	Bootable PCle-connected memory or storage computer device
US	61426542	N/A	Combinations of NVRAM and DRAM systems
US	61431442	N/A	protecting boot data against reflow and read disturb
US	61431444	N/A	Unified Flash and RAM
US	61432219	N/A	Data-Out Prediction and Pre Fetching in Bridged High Rate Systems
US	61435307	N/A	NVRAM partition
US	61436606	N/A	Use of Spare blocks for SLC cache
US	61436619	N/A	Verifying Program Operation
US	61440867	N/A	Recovery from Bit flip in memory system
US	61440868	N/A	Structured data mapping
US	61442252	N/A	Memory Protection Against WL Failure
US	61447111	N/A	Incremental redundancy codes
US	61447113	N/A	Adaptive memory partition between units
U5	61448201	N/A	Storage device with sideband interface for boot
US	61454584	N/A	Management Parity LBA separately partition

US	61454599	N/A	A storage system that exports multiple disk interface
US	61466941	N/A	MCP eMMC
US	61469854	N/A	Interference mitigation using individual word line erasure operations
US	61471257	N/A	Serial PPN
US	61472203	N/A	Memory system running scripts
US	61472629	N/A	Low Power SERDES Interface
US	61475241	N/A	data storage in analog memory cells using a non-integer number of bits per cell
US	61476287	N/A	SAS Target Performance optimizations
US	61482213	N/A	Provisional: LDPC Decoders interaction
US	61482216	N/A	Provisional: LDPC Double rate soft decoder
US	61486284	N/A	NAND LSB pages utilization
US	61486330	N/A	Sparse Programming Method
US	61486341	N/A	Advanced Programming Methods
US	61494916	N/A	Dual FTL
US	61497074	N/A	Cache block garbage collection
US	61528771	N/A	SAS Target Performance optimizations
US	61529267	N/A	Codes for multi-die redundancy
US	61529938	N/A	Provisional-Page mode FTL tables in SLC

US	61534389	N/A	IPR Proposals
US	61536597	N/A	Using dynamic mapping for die balancing in solid state drives
US	61536598	N/A	Selective secure erase in solid state drives
US	61537144	N/A	Optimized decoding of linear codes
US	61543813	N/A	Single Event Upset Protection in Cache Memories
US	61557428	N/A	Efficient Programming schemes to protect data from power failure during programming
US	12/880,101	Non-Publication	REUSE OF HOST HIBERNATION STORAGE SPACE BY MEMORY CONTROLLER
US	12/963,649	Non-Publication	Memory Management Schemes for Non-Volatile Memory Devices
US	12/987,174	Non-Publication	Redundant data storage in multi-die memory systems
US	12/987,175	Non-Publication	Redundant data storage in multi-die memory systems
US	13/021,754	Non-Publication	Reducing Peak Current in Memory Systems
US	13/047,822	Non-Publication	Data Storage Commands with Data Preceding Address
US	13/170,202	Non-Publication	ESTIMATION OF MEMORY CELL READ THRESHOLDS BY SAMPLING INSIDE PROGRAMMING LEVEL DISTRIBUTION INTERVALS

US		13/171,467	Non-Publication	Efficient Selection of Memory Blocks for Compaction
US		13/192,495	Non-Publication	Data storage at a non-integer number of bits per cell
US		13/192,504	Non-Publication	Interference mitigation in analog memory cells using individualword line erasure operations
US		13/284,913	20120044762	REJUVENATION OF ANALOG MEMORY CELLS
US	7,924,648	11/945,575	20080126686	MEMORY POWER AND PERFORMANCE MANAGEMENT
US	7,706,182	11/949,135	20080130341	ADAPTIVE PROGRAMMING OF ANALOG MEMORY CELLS
US	7,900,102	11/957,970	20080148115	HIGH-SPEED PROGRAMMING OF MEMORY DEVICES
US	7,593,263	11/958,011	20080158958	MEMORY DEVICE WITH REDUCED READING LATENCY
US	8,005,086	11/995,801	20080198650	Distortion estimation and cancellation in memory devices
US	7,821,826	11/995,805	20100110787	MEMORY CELL READOUT USING SUCCESSIVE APPROXIMATION
US	7,697,326	11/995,806	20090103358	REDUCING PROGRAMMING ERROR IN MEMORY DEVICES
US	7,466,575	11/995,811	20080198652	MEMORY DEVICE PROGRAMMING USING COMBINED SHAPING AND LINEAR SPREADING
US	8,151,163	11/995,812	20100115376	AUTOMATIC DEFECT MANAGEMENT IN MEMORY DEVICES

US	8,060,806	11/995,813	US20100131826	ESTIMATION OF NON-LINEAR DISTORTION IN MEMORY DEVICES
US	7,975,192	11/995,814	US20100165730	READING MEMORY CELLS USING MULTIPLE THRESHOLDS
US	8,156,403	11/996,054	20090024905	COMBINED DISTORTION ESTIMATION AND ERROR CORRECTION CODING FOR MEMORY DEVICES
US	7,751,240	12/019,011	20080181001	MEMORY DEVICE WITH NEGATIVE READ THRESHOLDS
US	8,151,166	12/037,487	20080219050	REDUCTION OF BACK PATTERN DEPENDENCY EFFECTS IN MEMORY DEVICES
US	8,001,320	12/045,520	20080263262	COMMAND INTERFACE FOR MEMORY DEVICES
US		12/063,544	20100157641	MEMORY DEVICE WITH ADAPTIVE CAPACITY
US		12/119,069	20080282106	DATA STORAGE WITH INCREMENTAL REDUNDANCY
US	7,925,936	12/171,797	Non-Publication	MEMORY DEVICE WITH NON-UNIFORM PROGRAMMING LEVELS
US	8,068,360	12/178,318	20090106485	READING ANALOG MEMORY CELLS USING BUILT-IN MULTI-THRESHOLD COMMANDS
US		12/186,867	20090043951	PROGRAMMING SCHEMES FOR MULTI-LEVEL ANALOG MEMORY CELLS
US	7,773,413	12/245,749	20090091979	RELIABLE DATA STORAGE IN ANALOG MEMORY CELLS IN THE PRESENCE OF TEMPERATURE VARIAIONS

US	8,000,141	12/251,471	Non-Publication	COMPENSATION FOR VOLTAGE DRIFTS IN ANALOG MEMORY CELLS
US		12/323,544	20090144600	EFFICIENT RE-READ OPERATIONS IN ANALOG MEMORY CELL ARRAYS
US		12/332,368	20090158126	EFFICIENT INTERFERENCE CANCELLATION IN ANALOG MEMORY CELL ARRAYS
US		12/332,370	20090157964	EFFICIENT DATA STORAGE IN MULTI-PLANE MEMORY DEVICES
US	8,085,586	12/344,233	20090168524	WEAR LEVEL ESTIMATION IN ANALOG MEMORY CELLS
US		12/355,817	20090187803	DECODING OF ERROR CORRECTION CODE USING PARTIAL BIT INVERSION
US	8,156,398	12/364,531	20090199074	PARAMETER ESTIMATION BASED ON ERROR CORRECTION CODE PARITY CHECK EQUATIONS
US	7,924,587	12/388,528	20090213653	programming of analog memory cells using a single programming pulse per state transition
US	7,864,573	12/390,522	20090213654	Programming analog memory cells for reduced variance after retention
US		12/397,368	20090228761	EFFICIENT READOUT FROM ANALOG MEMORY CELLS USING DATA COMPRESSION
US	8,059,457	12/405,275	20090240872	MEMORY DEVICE WITH MULTIPLE-ACCURACY READ COMMANDS
US		12/419,304	Non-Publication	HIGH-PERFORMANCE ECC DECODER

US	7,924,613	12/497,707	Non-Publication	DATA STORAGE IN ANALOG MEMORY CELLS WITH PROTECTION AGAINST PROGRAMMING INTERRUPTION
US		12/522,175	20100091535	ADAPTIVE ESTIMATION OF MEMORY CELL READ THRESHOLDS
US		12/534,893	Non-Publication	IMPROVED DATA STORAGE IN ANALOG MEMORY CELLS USING MODIFIED PASS VOLTAGES
US	7,995,388	12/534,898	Non-Publication	DATA STORAGEUSING MODIFIED VOLTAGES
US	8,169,825	12/551,567	Non-Publication	RELIABLE DATA STORAGE IN ANALOG MEMORY CELLS SUBJECTED TO LONG RETENTION PERIODS
US		12/551,583	Non-Publication	SEGMENTED DATA STORAGE
US	8,000,135	12/558,528	Non-Publication	ESTIMATION OF MEMORY CELL READ THRESHOLDS BY SAMPLING INSIDE PROGRAMMING LEVEL DISTRIBUTION INTERVALS
US		12/579,430	Non-Publication	EFFICIENT PROGRAMMING OF ANALOG MEMORY CELL DEVICES
US		12/579,432	Non-Publication	EFFICIENT DATA STORAGE IN STORAGE DEVICE ARRAYS
US		12/597,494	20100131827A1	MEMORY DEVICE WITH INTERNAL SIGNAL PROCESSING UNIT
US		12/607,078	Non-Publication	DATA SCRAMBLING IN MEMORY DEVICES
US		12/607,085	Non-Publication	DATA SCRAMBLING SCHEMES FOR MEMORY DEVICES

US		12/616,151	Non-Publication	CONFIGURABLE ENCODER FOR CYCLIC ERROR CORRECTION CODES
US		12/618,732	20100124088-A1	STORAGE AT M BITS/CELL DENSITY IN N BITS/CELL ANALOG MEMORY CELL DEVICES, M>N
US		12/649,358	Non-Publication	EFFICIENT READOUT SCHEMES FOR ANALOG MEMORY CELL DEVICES
US	8,174,857	12/649,360	Non-Publication	EFFICIENT READOUT SCHEMES FOR ANALOG MEMORY CELL DEVICES USING MULTIPLE READ THRESHOLD SETS
US		12/649,382	20100165689	REJUVENATION OF ANALOG MEMORY CELLS
US		12/677,114	20100199150	DATA STORAGE IN ANALOG MEMORY CELL ARRAYS HAVING ERASE FAILURES
US	÷	12/680,901	20100220510	OPTIMIZED SELECTION OF MEMORY UNITS IN MULTI-UNIT MEMORY DEVICES
US		12/688,883	Non-Publication	HIERARCHICAL DATA STORAGE SYSTEM
US		12/714,501	20100220509	SELECTIVE ACTIVATION OF PROGRAMMING SCHEMES IN ANALOG MEMORY CELL ARRAYS
US	8,174,905	12/721,585	20100157675	PROGRAMMING ORDERS FOR REDUCING DISTORTION IN ARRAYS OF MULTI-LEVEL ANALOG MEMORY CELLS
US		12/728,287	20100250836	USE OF HOST SYSTEM RESOURCES BY MEMORY CONTROLLER
US		12/728,289	Non-Publication	Dual ECC decoder

ÜS		12/728,296	Non-Publication	DATABASE OF MEMORY READ THRESHOLDS
US		12/758,003	Non-Publication	Selective re-programming of analog memory cells
US	7,881,107	12/758,044	20100195390	MEMORY DEVICE WITH NEGATIVE READ THRESHOLDS
US		12/797,615	20100332955A1	Chien search using multiple basis representation
US		12/822,207	Non-Publication	ADAPTIVE OVER-PROVISIONING IN MEMORY SYSTEMS
US		12/843,029	Non-Publication	Efficient LDPC codes
US		12/876,170	Non-Publication	EFFICIENT STORAGE OF ERROR CORRECTION INFORMATION IN DRAM
US		12/890,724	Non-Publication	ERROR CORRECTION CODING OVER MULTIPLE MEMORY PAGES
US		12/913,815	Non-Publication	Termination Criteria for Iterative Decoders
US		13/069,406	Non-Publication	Cache memory for hybrid disk drives
US		13/088,361	Non-Publication	Read commands for reading interfering memory cells
US	8,145,984	13/114,049	US20110225472A1	READING MEMORY CELLS USING MULTIPLE THRESHOLDS
US		13/171,761	Non-Publication	Interference-aware assignment of programming levels in analog memory cells
US		13/192,501	Non-Publication	Data storage at a non-integer number of bits per cell
US		13/195,852	Non-Publication	Read threshold setting based on soft readout statistics

US	13/214,257	Non-Publication	MEMORY DEVICE WITH MULTIPLE-ACCURACY READ COMMANDS
US	13/231,963	Non-Publication	Memory Management For Unifying Memory Cell Conditions
US	13/239,408	20120026788	Distortion estimation and cancellation in memory devices
US	13/239,411	20120026789	Distortion estimation and cancellation in memory devices
US	13/284,909	Non-Publication	MEMORY DEVICE WITH MULTIPLE-ACCURACY READ COMMANDS
US	13/338,335	Non-Publication	Sparse programming of Analog Memory Celles
US	13/355,536	Non-Publication	Block Management Schemes in Hybrid SLC/MLC Memory
US	13/356,694	Non-Publication	Advanced Programming Verification Schemes for Analog Memory Cells
US	13/371,443	Non-Publication	Protection Against Word Line Failure in Memory Devices
US	13/405,308	N/A	Error Correction Codes for Incremental Redundancy
US	13/405,309	N/A	AUTOMATIC DEFECT MANAGEMENT IN MEMORY DEVICES
US	13/412,731	N/A	Programming orders for reducing distortion based on neighboring rows
US	13/412,780	N/A	Reducing distortion using joint storage

US	13/419,452	N/A	Independent Management of Data and Parity Logical Block Addresses
US	13/419,453	N/A	Storage System Exporting Internal Storage Rules
US	13/426,799	N/A	Selective Date Storage in LSB and MSB Pages
US	13/429,385	N/A	Redundant Storage in Non-Volatile Memory by Storing Redundacy Information in Volatile Memory
US	13/439,860	N/A	Efficient connection management in a SAS target
US	13/439,863	N/A	High-performance SAS target
US	13/471,483	N/A	ENHANCED PROGRAMMING AND ERASURE SCHEMES FOR ANALOG MEMORY CELLS
US	13/471,484	N/A	PROGRAMMING AND ERASURE SCHEMES FOR ANALOG MEMORY CELLS
PCT	PCT/IB2012/052375	N/A	Sparse programming of Analog Memory Cells
PCT	PCT/IB2012/052376	N/A	Selective Date Storage in LSB and MSB Pages
PCT	PCT/IL2007/000575	WO 2007/132452	REDUCING PROGRAMMING ERROR IN MEMORY DEVICES
PCT	PCT/IL2007/000576	WO 2007/132453	Distortion estimation and cancellation in memory devices
PCT	PCT/IL2007/000579	WO 2007/132456	MEMORY DEVICE WITH ADAPTIVE CAPACITY
PCT	PCT/IL2007/000580	WO 2007/132457	COMBINED DISTORTION ESTIMATION AND ERROR CORRECTION CODING FOR MEMORY DEVICES

PCT	PCT/IL2007/000581	WO 2007/132458	MEMORY DEVICE PROGRAMMING USING COMBINED SHAPING AND LINEAR SPREADING
PCT	PCT/IL2007/001059	WO 2008/026203	ESTIMATION OF NON-LINEAR DISTORTION IN MEMORY DEVICES
PCT	PCT/IL2007/001315	WO 2008/053472	READING MEMORY CELLS USING MULTIPLE THRESHOLDS
PCT	PCT/IL2007/001316	WO 2008/053473	MEMORY CELL READOUT USING SUCCESSIVE APPROXIMATION
PCT	PCT/IL2007/001488	WO 2008/068747	AUTOMATIC DEFECT MANAGEMENT IN MEMORY DEVICES
PCT	PCT/IL2008/000176 (Cancelled)	N/A	MEMORY DEVICE WITH NON-UNIFORM PROGRAMMING LEVELS
PCT	PCT/IL2008/000329	WO 2008/111058	ADAPTIVE ESTIMATION OF MEMORY CELL READ THRESHOLDS
PCT	PCT/IL2008/000519	WO 2008/139441	MEMORY DEVICE WITH INTERNAL SIGNAL PROCESSING UNIT
PCT	PCT/IL2008/001188	WO/2009/037691	PROGRAMMING ORDERS FOR REDUCING DISTORTION IN ARRAYS OF MULTI-LEVEL ANALOG MEMORY CELLS
PCT	PCT/IL2008/001356	WO/2009/050703	DATA STORAGE IN ANALOG MEMORY CELL ARRAYS HAVING ERASE FAILURES
PCT	PCT/IL2008/001446	WO/2009/063450	OPTIMIZED SELECTION OF MEMORY UNITS IN MULTI-UNIT MEMORY DEVICES

KR	10-2008-7028793	N/A	COMBINED DISTORTION ESTIMATION AND ERROR CORRECTION CODING FOR MEMORY DEVICES
KR	10-2008-7028919	N/A	MEMORY DEVICE WITH ADAPTIVE CAPACITY
KR	10-2008-7029297	N/A	Distortion estimation and cancellation in memory devices
KR	10-2010-7006449	N/A	OPTIMIZED SELECTION OF MEMORY UNITS IN MULTI-UNIT MEMORY DEVICES
JP	2009-508668	N/A	MEMORY DEVICE WITH ADAPTIVE CAPACITY
JP	20090318085550-m1	N/A	COMBINED DISTORTION ESTIMATION AND ERROR CORRECTION CODING FOR MEMORY DEVICES
CN	200780026181.3	CN101512661A	COMBINED DISTORTION ESTIMATION AND ERROR CORRECTION CODING FOR MEMORY DEVICES
CN	200880005741.1	CN101715595A	ADAPTIVE ESTIMATION OF MEMORY CELL READ THRESHOLDS
CN	2011102948683	CN102394101A	MEMORY DEVICE WITH ADAPTIVE CAPACITY
CN	200780026094.8 .	CN101501779A	MEMORY DEVICE WITH ADAPTIVE CAPACITY
CN	200780026121.1.	CN101496110A	Distortion estimation and cancellation in memory devices
CN	200780040493X	CN101601094A	READING MEMORY CELLS USING MULTIPLE THRESHOLDS

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